

Notice of References Cited	Application/Control No. 10/621,488		Applicant(s)/Patent Under Reexamination YAMAGUCHI, HITOSHI	
	Examiner Anh D. Mai		Art Unit 2814	Page 1 of 1

U.S. PATENT DOCUMENTS

*		Document Number Country Code-Number-Kind Code	Date MM-YYYY	Name	Classification
*	A	US-5,045,900	09-1991	Tamagawa, Akio	257/338
*	B	US-5,349,224 A	09-1994	Gilbert et al.	257/341
*	C	US-5,640,034	06-1997	Malhi, Satwinder	257/341
*	D	US-5,739,572 A	04-1998	Noguchi, Ko	257/338
*	E	US-6,060,731 A	05-2000	Murata et al.	257/330
*	F	US-6,211,549 B1	04-2001	Funaki et al.	257/330
*	G	US-6,323,518 B1	11-2001	Sakamoto et al.	257/330
*	H	US-6,452,231 B1	09-2002	Nakagawa et al.	257/343
*	I	US-6,525,375	02-2003	Yamaguchi et al.	257/341
*	J	US-6,555,872 B1	04-2003	Dennen, Michael W.	257/327
	K	US-			
	L	US-			
	M	US-			

FOREIGN PATENT DOCUMENTS

*		Document Number Country Code-Number-Kind Code	Date MM-YYYY	Country	Name	Classification
*	N	JP-09-129868	05-1997	Japan	Ninomiya, Hitoshi	H01L 29/78
*	O	JP-2000-150664	05-2000	Japan	Nakagawa, Akio	H01L 21/8234
	P					
	Q					
	R					
	S					
	T					

NON-PATENT DOCUMENTS

*		Include as applicable: Author, Title Date, Publisher, Edition or Volume, Pertinent Pages)
	U	B. J. Baliga et al., Gate Turn-Off Capability of Depletion-Mode Thyristors. 1989 IEEE, pp. 464-466.
	V	K.G.P. Dharmawardana et al., Analytical Model for High Current Density Trench Gate MOSFET. Proceedings of 1998 International Symposium on Power Semiconductor Devices & ICs, Kyoto, pp. 351-354.
	W	A. Nakagawa et al., Improved 20V Lateral Trench Gate Power MOSFETs with Very Low On-Resistance of 7.8 mOhm.mm ² . 2000 IEEE, pp. 47-50.
	X	A. Narazaki et al., A 0.35 micron Trench Gate MOSFET with An Ultra Low On State Resistance and A High Destruction Immunity During the Inductive Switching. 2000 IEEE, pp. 377-380.

*A copy of this reference is not being furnished with this Office action. (See MPEP § 707.05(a).)
Dates in MM-YYYY format are publication dates. Classifications may be US or foreign.